

N-Channel Enhancement Mode Power MOSFET

Description

The PE0213 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

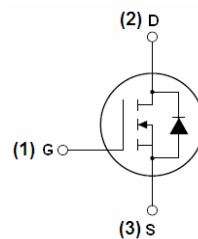
General Features

- $V_{DS} = 200V, I_D = 13A$
 $R_{DS(ON)} < 140m\Omega @ V_{GS}=10V$ (Typ:123m Ω)

- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Boost converters
- LED backlighting
- Uninterruptible power supply



Schematic diagram



TO-220-3L top view

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	13	A
$I_D (100^\circ\text{C})$	Drain Current-Continuous($T_C=100^\circ\text{C}$)	9	A
I_{DM}	Pulsed Drain Current	45	A
P_D	Maximum Power Dissipation	95	W
	Derating factor	0.6	W/ $^\circ\text{C}$
E_{AS}	Single pulse avalanche energy ^(Note 5)	200	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	$^\circ\text{C}$

Thermal Characteristic

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case ^(Note 2)	1.6	°C/W
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol		Parameter	Condition	Min	Typ	Max	Unit
Off Characteristics							
BV _{DSS}	Drain-Source Breakdown Voltage		V _{GS} =0V I _D =250μA	200	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current		V _{DS} =200V, V _{GS} =0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current		V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)							
V _{GS(th)}	Gate Threshold Voltage		V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
R _{DS(ON)}	Drain-Source On-State Resistance		V _{GS} =10V, I _D =8A	-	123	140	mΩ
g _{FS}	Forward Transconductance		V _{DS} =10V, I _D =8A	-	6	-	S
Dynamic Characteristics ^(Note4)							
C _{iss}	Input Capacitance		V _{DS} =25V, V _{GS} =0V, F=1.0MHz	-	2000	-	PF
C _{oss}	Output Capacitance			-	260	-	PF
C _{rss}	Reverse Transfer Capacitance			-	150	-	PF
Switching Characteristics ^(Note 4)							
t _{d(on)}	Turn-on Delay Time		V _{DD} =100V, R _G =8Ω V _{GS} =10V, I _D =8A	-	11.5	-	nS
t _r	Turn-on Rise Time			-	22	-	nS
t _{d(off)}	Turn-Off Delay Time			-	18	-	nS
t _f	Turn-Off Fall Time			-	10	-	nS
Q _g	Total Gate Charge		V _{DS} =160V, I _D =8A, V _{GS} =10V	-	27	-	nC
Q _{gs}	Gate-Source Charge			-	4.4	-	nC
Q _{gd}	Gate-Drain Charge			-	11.6	-	nC
Drain-Source Diode Characteristics							
V _{SD}	Diode Forward Voltage ^(Note 3)		V _{GS} =0V, I _S =8A	-	-	1.2	V
I _S	Diode Forward Current ^(Note 2)		-	-	-	13	A
t _{rr}	Reverse Recovery Time		T _J = 25°C, I _F = 8A di/dt = 100A/μs ^(Note3)	-	32	-	nS
Q _{rr}	Reverse Recovery Charge			-	53	-	nC
t _{on}	Forward Turn-On Time		Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25\Omega$

Typical Electrical and Thermal Characteristics (Curves)

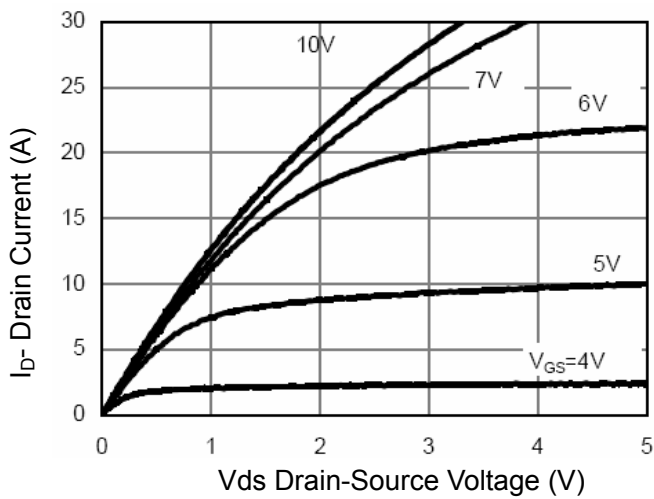


Figure 1 Output Characteristics

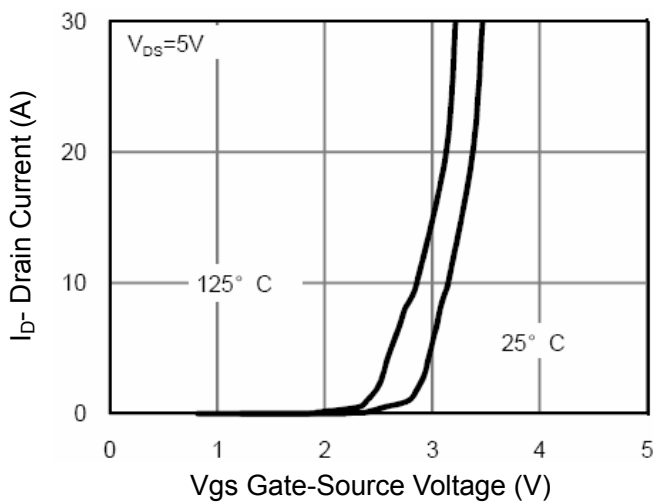


Figure 2 Transfer Characteristics

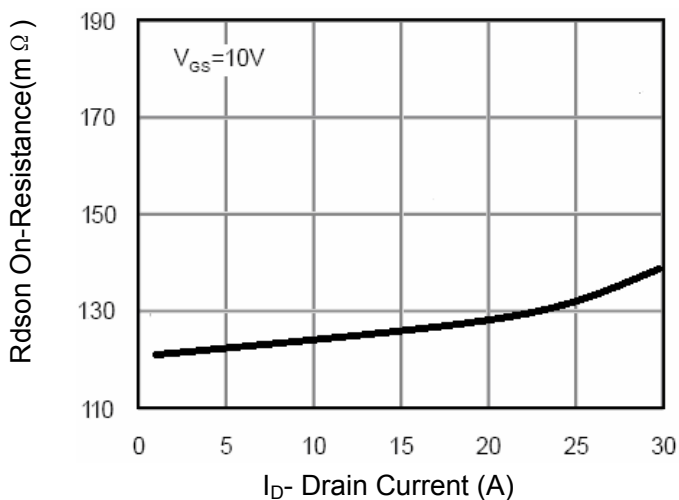


Figure 3 $R_{DS(on)}$ - Drain Current

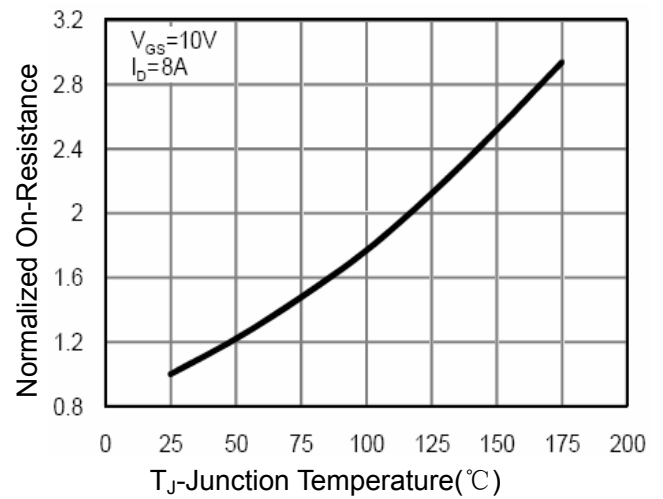


Figure 4 $R_{DS(on)}$ -Junction Temperature

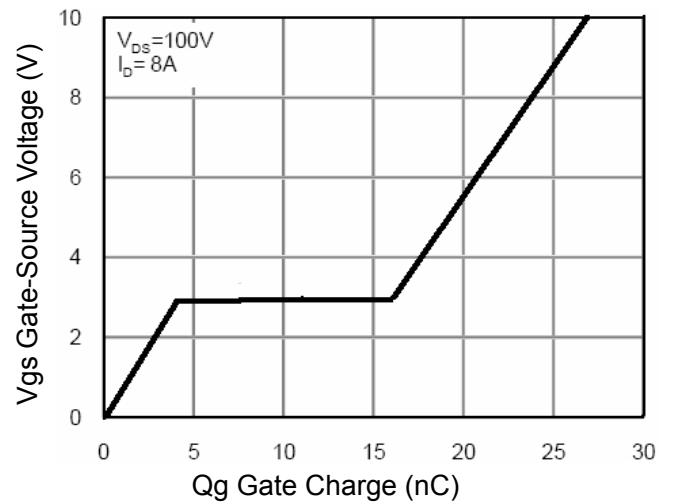


Figure 5 Gate Charge

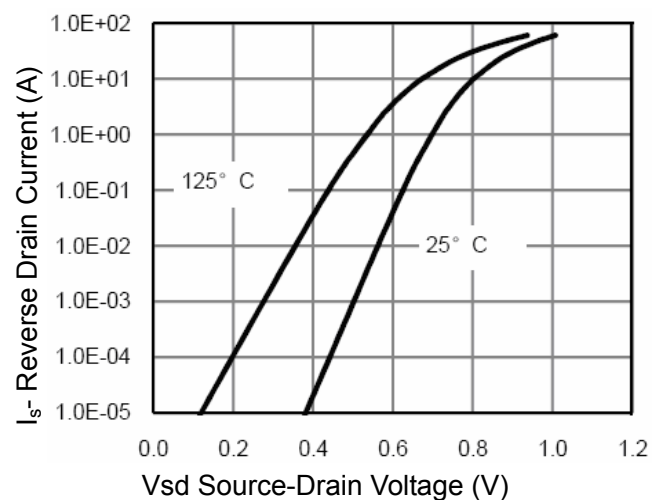


Figure 6 Source- Drain Diode Forward

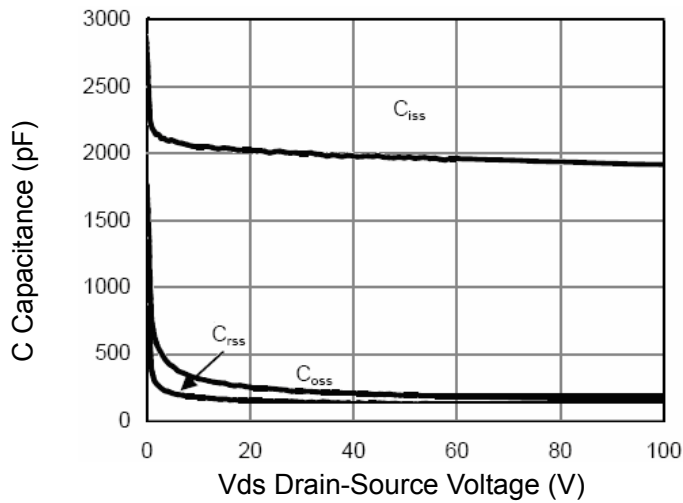


Figure 7 Capacitance vs Vds

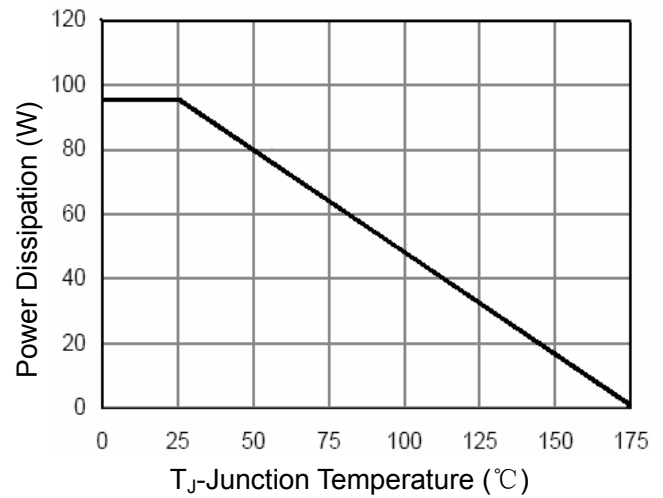


Figure 9 Power De-rating

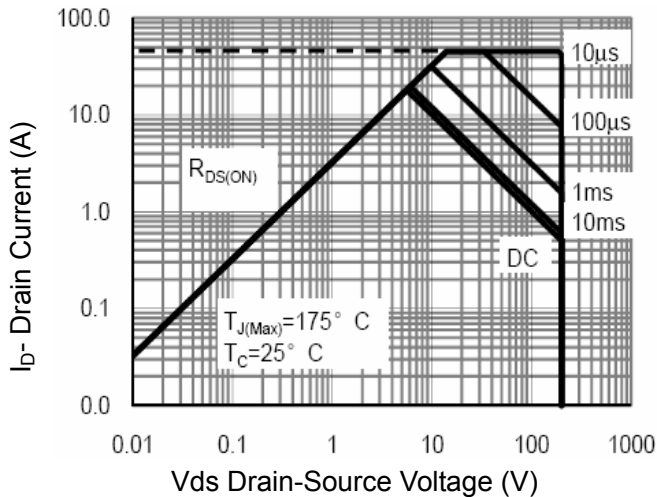


Figure 8 Safe Operation Area

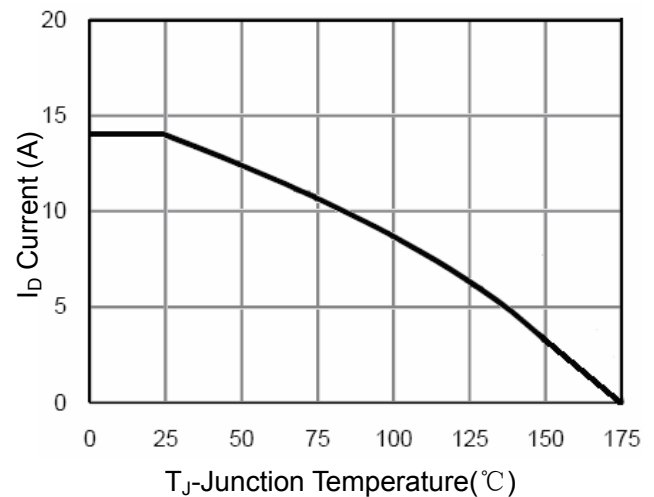


Figure 10 ID Current- Junction Temperature

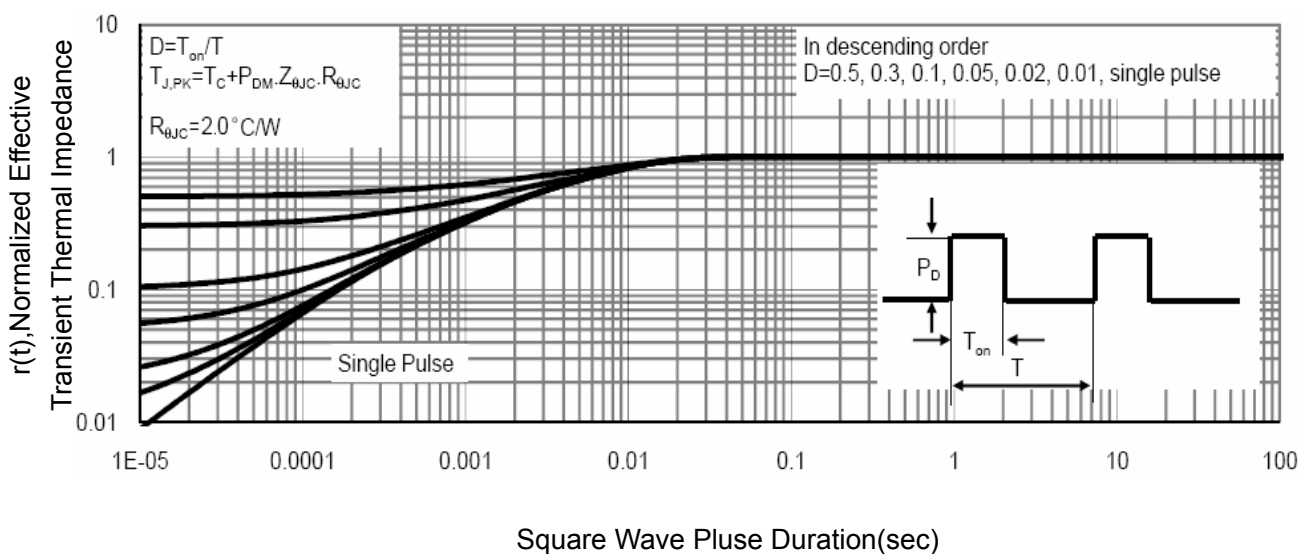
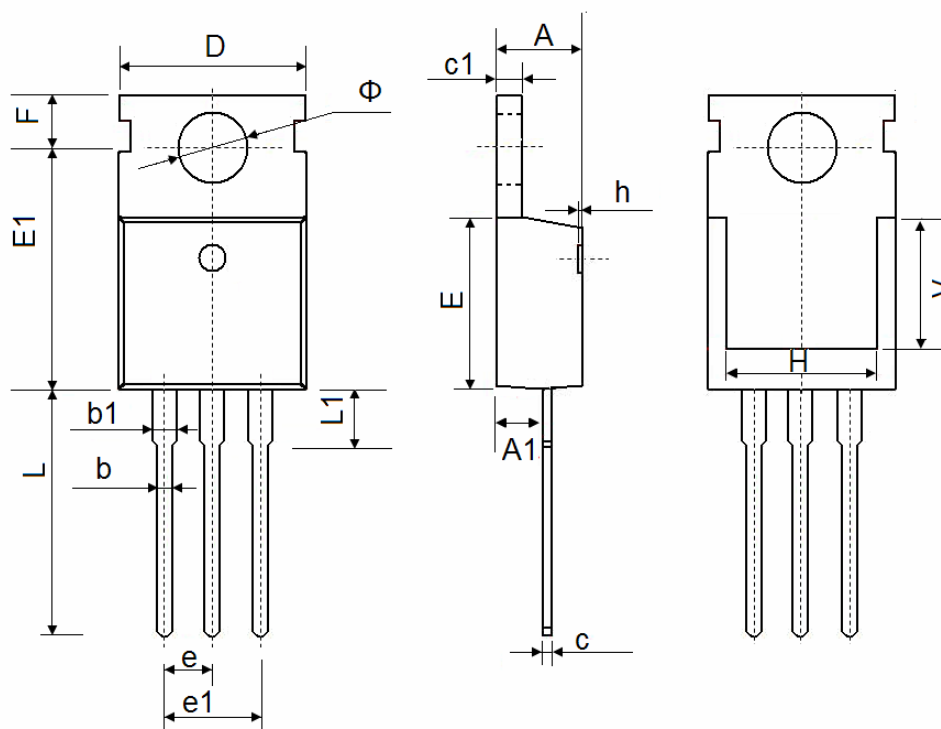


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150